

Title (en)
SEMICONDUCTOR PACKAGING

Title (de)
HALBLEITERGEHÄUSUNG

Title (fr)
ENCAPSULATION DE SEMI-CONDUCTEURS

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Application
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Abstract (en)
[origin: WO0124259A2] An electronic component and a method for making an electronic component are disclosed. The electronic component has a silicon package. The silicon package has a recess formed thereon in which a conductive region is placed. A bare die electronic device is disposed in the recess. The device has a top, a bottom, sides and a plurality of terminals, including a non-top terminal. The non-top terminal is electrically coupled to the conductive region. The electronic component is constructed by first creating a recess in a silicon wafer to a depth substantially equal to the first dimension of the bare die electronic device. A conductive material is applied to the recess. The electronic device is inserted into the recess so that the bottom terminal is coupled to the conductive material. A dielectric or other planarizing material is applied into the recess. Top and bottom contacts are then applied to form the electronic component so that it may be used as a ball grid array package. The top contact is electrically coupled to the top terminal of the electronic device and the bottom contact is coupled electrically to the conductive material.

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Citation (search report)
See references of WO 0124259A2

Citation (examination)
• JP S61214444 A 19860924 - FUJITSU LTD
• EP 0288052 A2 19881026 - SUMITOMO ELECTRIC INDUSTRIES [JP]
• JP S5944849 A 19840313 - HITACHI LTD, et al

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